MGFC40V5964

5.9 ~ 6.4GHz BAND 10W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC40V3742 is an internally impedance-matched GaAs power FET especially designed for use in 5.9 ~ 6.4 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation Internally matched to 50(ohm) system High output power P1dB = 10W (TYP.) @ f=5.9 - 6.4GHz High power gain GLP = 10 dB (TYP.) @ f=5.9 - 6.4GHz High power added efficiency P.A.E. = 30 % (TYP.) @ f=5.9 - 6.4GHz Low distortion [item -51] IM3= -49 dBc(TYP.) @ Po=29(dBm) S.C.L.

APPLICATION

item 01 : 5.9~6.4 GHz band power amplifier item 51 : 5.9~6.4 GHz band digital radio communication

QUALITY GRADE

IG

RECOMMENDED BIAS CONDITIONS

VDS = 10(V)ID = 2.4 (A)Rg = 50(ohm) Refer to Bias Procedure

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Ratings	Unit	
VGDO	Gate to drain voltage	-15	V	
VGSO	Gate to source voltage	-15	V	
ID	Drain current	7.5	Α	
IGR	Reverse gate current	-20	mA	
IGF	Forward gate current	42	mA	
PT	Total power dissipation *1	42.8	W	
Tch	Channel temperature	175	deg.C	
Tstg	Storage temperature	-65 / +175	deg.C	

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*1 : Tc=25 deg.C

ELECTRICAL CHARACTERISTICS (Ta=25 deg.C)

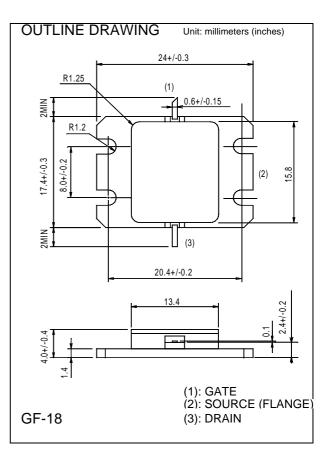
Symbol	Parameter	Test conditions	Limits			Unit
Symbol	Falallelel	Test conditions	Min.	Тур.	Max.	Unit
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	4.5	6	Α
gm	Transconductance	VDS=3V, ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=40mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression		39.5	40.5	-	dBm
GLP	Linear power gain	VDS=10V, ID(RF off)=2.4A, f=5.9~6.4GHz	8	10	-	dB
ID	Drain current		-	2.4	-	Α
P.A.E.	Power added efficiency		-	30	-	%
IM3	3rd order IM distortion *1		-42	-49	-	dBc
Rth(ch-c)	Thermal resistance *2	Delta Vf method	-	3	3.5	deg.C/W

(Ta=25 deg.C)

*1 : item -51, 2 tone test, Po=29dBm Single Carrier Level, f=6.4GHz, Delta f=10MHz

*2 : Channel to case





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